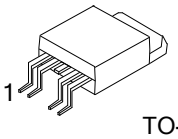
DUAL MIDDLE POWER MOSFET (N-CHANNEL/P-CHANNEL)



TO-252-4

■ DESCRIPTION

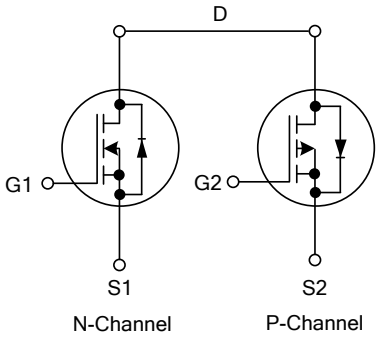
The UTC **UT18NP10** incorporates an N-channel MOSFET and a P-channel MOSFET，it uses UTC's advanced technology to provide customers a minimum on-state resistance and high-speed switching, thereby enabling high-density mounting.

The UTC **UT18NP10** is universally applied in high-speed switching, motor driver.

■ FEATURES

* N-Channel
  $R_{DS(on)}$ ≤ 60 mΩ @ V_{GS}=10V, I_D=4.5A
  $R_{DS(on)}$ ≤ 68 mΩ @ V_{GS}=4.5V, I_D=4.5A
* P-Channel
  $R_{DS(on)}$ ≤ 220 mΩ @ V_{GS}=-10V, I_D=-4.5A
  $R_{DS(on)}$ ≤ 250 mΩ @ V_{GS}=-4.5V, I_D=-4.5A
* High switching speed

■ SYMBOL



■ ORDERING INFORMATION

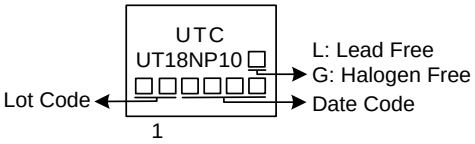
Ordering Number		Package	Pin Assignment					Packing
Lead Free	Halogen Free		1	2	3	4	5	
UT18NP10L-TN4-R	UT18NP10G-TN4-R	TO-252-4	S1	G1	D	S2	G2	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT18NP10G-TN4-R
(1)Packing Type
(2)Package Type
(3)Green Package

(1) R: Tape Reel
(2) TN4: TO-252-4
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS		UNIT
				N-CH	P-CH	
Drain-Source Voltage			V_{DSS}	100	-100	V
Gate-Source Voltage			V_{GSS}	±20	±20	V
Drain Current	Continuous	T_C=25°C	I_D	9	-9	A
	Pulsed		I_{DM}	18	-18	A
Avalanche Energy, Single Pulse			E_{AS}	67.3	35.9	mJ
Power Dissipation			P_D	44		W
Junction Temperature			T_J	+150		°C
Range of Storage Temperature			T_{STG}	-55 ~ +150		°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. N-Channel: L=0.1mH, I_{AS}=36.7A, V_{DD}=25V, R_G=25Ω, Starting T_J=25°C
P-Channel: L=0.1mH, I_{AS}=-26.8A, V_{DD}=-50V, R_G=25Ω, Starting T_J=25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.85 (Note)	°C/W

Note: The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

N-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.0		3.0	V
Static Drain-Source On-State Resistance (Pulsed)	$R_{DS(ON)}$	V_{GS}=10V, I_D=4.5A			60	mΩ
		V_{GS}=4.5V, I_D=4.5A			68	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		3000		pF
Output Capacitance	C_{OSS}			155		pF
Reverse Transfer Capacitance	C_{RSS}			140		pF
SWITCHING PARAMETERS						
Total Gate Charge (Pulsed)	Q_G	V_{DD}=80V, V_{GS}=10V, I_D=9A I_G=1mA (Note 1, 2)		62		nC
Gate to Source Charge (Pulsed)	Q_{GS}			8.5		nC
Gate to Drain Charge (Pulsed)	Q_{GD}			14		nC
Turn-ON Delay Time (Pulsed)	$t_{D(ON)}$	V_{DD}=50V, V_{GS}=10V, I_D=9A, R_G=3Ω (Note 1, 2)		27		ns
Rise Time (Pulsed)	t_R			19		ns
Turn-OFF Delay Time (Pulsed)	$t_{D(OFF)}$			74		ns
Fall-Time (Pulsed)	t_F			19		ns
SOURCE TO DRAIN DIODE SPECIFICATIONS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				9	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				18	A
Diode Forward Voltage	V_{SD}	I_S=9.0A, V_{GS}=0V			1.4	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ ELECTRICAL CHARACTERISTICS (Cont.)

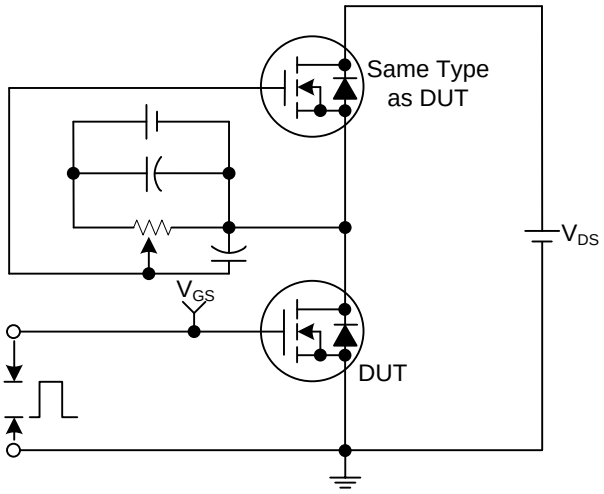
P-CHANNEL

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA, V_{GS}=0V	-100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V, V_{GS}=0V			-1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0		-3.0	V
Static Drain-Source On-State Resistance (Pulsed)	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-4.5A			220	mΩ
		V_{GS}=-4.5V, I_D=-4.5A			250	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=-25V, f=1.0MHz		1430		pF
Output Capacitance	C_{OSS}			85		pF
Reverse Transfer Capacitance	C_{RSS}			72		pF
SWITCHING PARAMETERS						
Total Gate Charge (Pulsed)	Q_G	V_{DD}=-80V, V_{GS}=-10V, I_D=-9A I_G=-1mA (Note 1, 2)		34		nC
Gate to Source Charge (Pulsed)	Q_{GS}			5.4		nC
Gate to Drain Charge (Pulsed)	Q_{GD}			7.6		nC
Turn-ON Delay Time (Pulsed)	$t_{D(ON)}$	V_{DD}=-50V, V_{GS}=-10V, I_D=-9A, R_G=3Ω (Note 1, 2)		20		ns
Rise Time (Pulsed)	t_R			15		ns
Turn-OFF Delay Time (Pulsed)	$t_{D(OFF)}$			53		ns
Fall-Time (Pulsed)	t_F			16		ns
SOURCE TO DRAIN DIODE SPECIFICATIONS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				-9	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				-18	A
Diode Forward Voltage	V_{SD}	I_S=-9.0A,V_{GS}=0V			-1.4	V

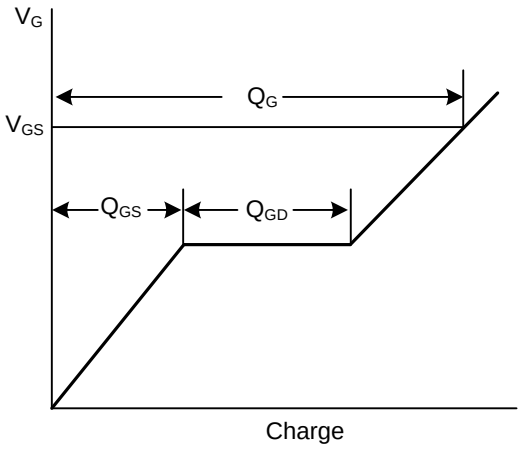
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

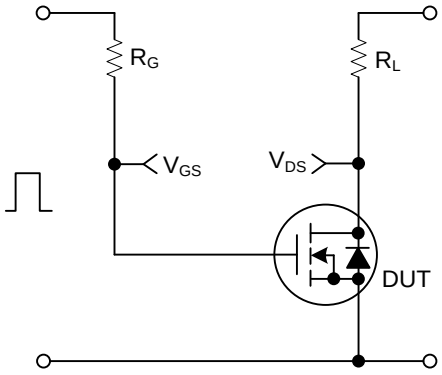
N-CHANNEL



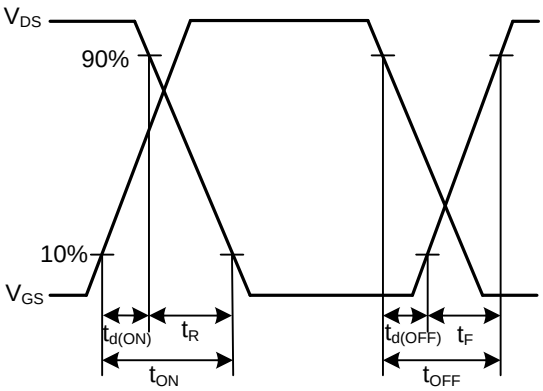
Gate Charge Test Circuit



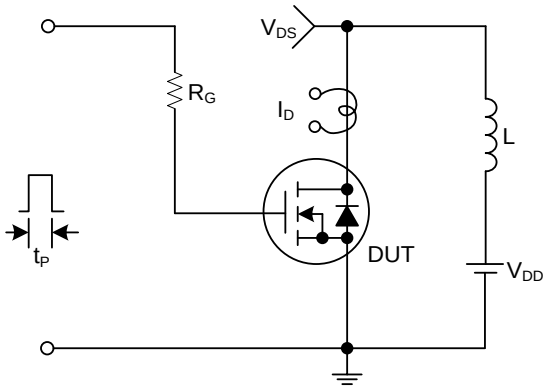
Gate Charge Waveforms



Resistive Switching Test Circuit

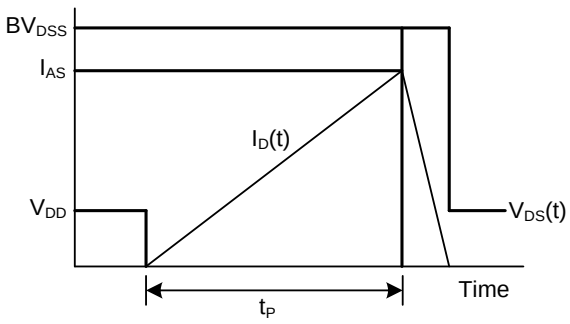


Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

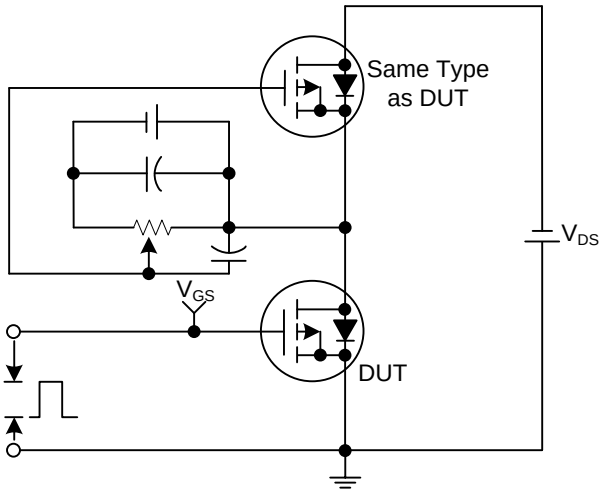
$$E_{AS}=\frac{1}{2}LI_{AS}^2\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$



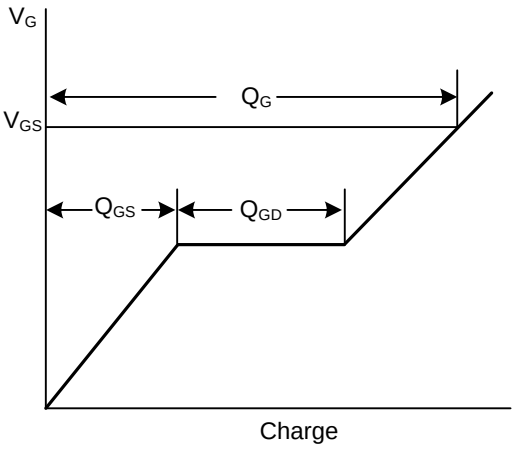
Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS

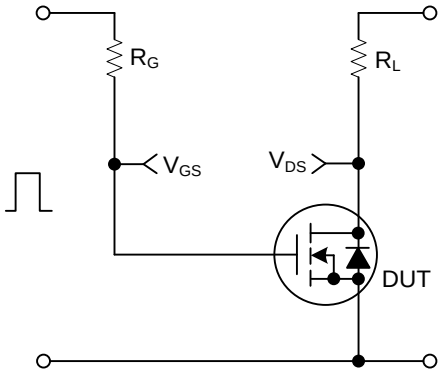
P-CHANNEL



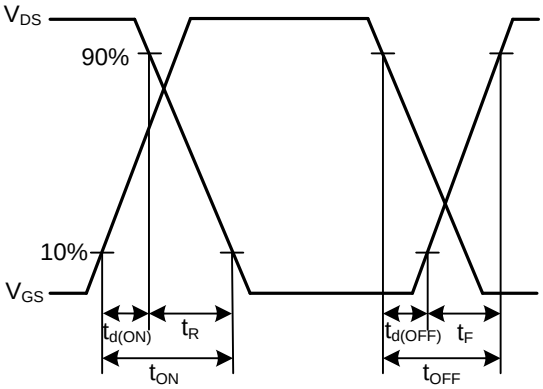
Gate Charge Test Circuit



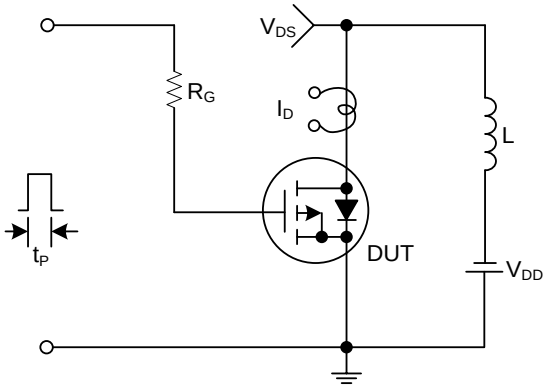
Gate Charge Waveforms



Resistive Switching Test Circuit

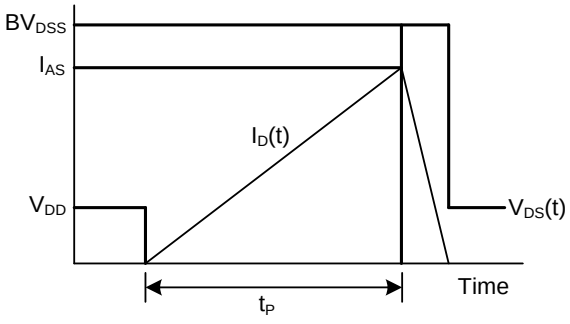


Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

$$E_{AS}=\frac{1}{2}LI_{AS}^{2}\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$



Unclamped Inductive Switching Waveforms